Achim Trampert

List of Publications by Year
in descending order

261 papers	8,843 citations	53660 45 h-index	56606 83 g-index
265 all docs	265 docs citations	265 times ranked	6527 citing authors

#	Article	IF	Citations
1	Nitride semiconductors free of electrostatic fields for efficient white light-emitting diodes. Nature, 2000, 406, 865-868.	13.7	1,662
2	Origin of high-temperature ferromagnetism in (Ga,Mn)N layers grown on 4Hâ€“SiC(0001) by reactive molecular-beam epitaxy. Applied Physics Letters, 2003, 82, 2077-2079.	1.5	197
3	On the mechanisms of spontaneous growth of III-nitride nanocolumns by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 4035-4045.	0.7	165
4	Wurtzite GaN nanocolumns grown on Si(001) by molecular beam epitaxy. Applied Physics Letters, 2006, 88, 213114.	1.5	153
5	Growth, morphology, and structural properties of group-III-nitride nanocolumns and nanodisks. Physica Status Solidi (B): Basic Research, 2007, 244, 2816-2837.	0.7	148
6	High resolution transmission electron microscopy studies of the Ag/MgO interface. Acta Metallurgica Et Materialia, 1992, 40, S227-S236.	1.9	144
7	Impact of nucleation conditions on the structural and optical properties ofM-plane GaN(11Ì„00) grown on Î³-LiAlO2. Journal of Applied Physics, 2002, 92, 5714-5719.	1.1	143
8	Continuous-flux MOVPE growth of position-controlled N-face GaN nanorods and embedded InGaN quantum wells. Nanotechnology, 2010, 21, 305201.	1.3	142
9	Correlation of structure and magnetism in GaAs with embedded Mn(Ga)As magnetic nanoclusters. Journal of Applied Physics, 2002, 92, 4672-4677.	1.1	130
10	The nanorod approach: GaN NanoLEDs for solid state lighting. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2296-2301.	0.8	128
11	Metalâ€“Semiconductor Phaseâ€Transition in WSe_{2(1â€‹}<i>_x</i>₎Te₂<i>_x</i> Monolayer. Advanced Materials, 2017, 29, 1603991.	11.1	123
12	Clustering in a Precipitate-Free GeMn Magnetic Semiconductor. Physical Review Letters, 2006, 97, 237202.	2.9	122
13	Influence of AlN nucleation layers on growth mode and strain relief of GaN grown on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 74, 3660-3662.	1.5	113
14	Coaxial Multishell (In,Ga)As/GaAs Nanowires for Near-Infrared Emission on Si Substrates. Nano Letters, 2014, 14, 2604-2609.	4.5	111
15	Spontaneous Nucleation and Growth of GaN Nanowires: The Fundamental Role of Crystal Polarity. Nano Letters, 2012, 12, 6119-6125.	4.5	106
16	Polarity in GaN and ZnO: Theory, measurement, growth, and devices. Applied Physics Reviews, 2016, 3, .	5.5	105
17	Understanding the selective area growth of GaN nanocolumns by MBE using Ti nanomasks. Journal of Crystal Growth, 2011, 325, 89-92.	0.7	97
18	Direct experimental determination of the spontaneous polarization of GaN. Physical Review B, 2012, 86, .	1.1	94

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19	Critical issues for the growth of high-quality (Al,Ga)N/GaN and GaN/(In,Ga)N heterostructures on SiC(0001) by molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 4019-4021.	1.5	88
20	Effects of nanowire coalescence on their structural and optical properties on a local scale. Applied Physics Letters, 2009, 95, .	1.5	84
21	Quantitative description for the growth rate of self-induced GaN nanowires. Physical Review B, 2012, 85, .	1.1	80
22	Molecular beam epitaxy of single crystalline GaN nanowires on a flexible Ti foil. Applied Physics Letters, 2016, 108, .	1.5	79
23	Direct observation of the initial nucleation and epitaxial growth of metastable cubic GaN on (001) GaAs. Applied Physics Letters, 1997, 70, 583-585.	1.5	78
24	Determination of the azimuthal orientational spread of GaN films by x-ray diffraction. Applied Physics Letters, 2002, 81, 4928-4930.	1.5	73
25	Molecular Beam Epitaxy of GaN Nanowires on Epitaxial Graphene. Nano Letters, 2017, 17, 5213-5221.	4.5	72
26	ColumnarAlGaN/GaNNanocavities withAlN/GaNBragg Reflectors Grown by Molecular Beam Epitaxy on Si(111). Physical Review Letters, 2005, 94, 146102.	2.9	71
27	Patterned growth on highâ€index GaAs (n11) substrates: Application to sidewall quantum wires. Journal of Applied Physics, 1996, 80, 4108-4111.	1.1	64
28	Growth of M-Plane GaN(11-00): A Way to Evade Electrical Polarization in Nitrides. Physica Status Solidi A, 2000, 180, 133-138.	1.7	64
29	Novel plastic strainâ€relaxation mode in highly mismatched IIIâ€V layers induced by twoâ€dimensional epitaxial growth. Applied Physics Letters, 1995, 66, 2265-2267.	1.5	63
30	Macro- and micro-strain in GaN nanowires on Si(111). Nanotechnology, 2011, 22, 295714.	1.3	61
31	Phase-transition-induced residual strain in ferromagnetic MnAs films epitaxially grown on GaAs(001). Applied Physics Letters, 2001, 78, 2461-2463.	1.5	60
32	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. Journal of Applied Physics, 2003, 94, 2319-2324.	1.1	60
33	Self Assembled InAs/InP Quantum Dots for Telecom Applications in the 1.55 Âµm Wavelength Range: Wavelength Tuning, Stacking, Polarization Control, and Lasing. Japanese Journal of Applied Physics, 2006, 45, 6544-6549.	0.8	60
34	Scaling growth kinetics of self-induced GaN nanowires. Applied Physics Letters, 2012, 100, .	1.5	60
35	Nonuniform segregation of Ga at AlAs/GaAs heterointerfaces. Physical Review B, 1997, 55, 1689-1695.	1.1	59
36	Phase formation and strain relaxation of Ga2O3 on c-plane and a-plane sapphire substrates as studied by synchrotron-based x-ray diffraction. Applied Physics Letters, 2017, 111, .	1.5	58

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37	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. Applied Physics Letters, 2004, 84, 2503-2505.	1.5	57
38	Micro-Photoluminescence Study at Room Temperature of Sidewall Quantum Wires Formed on Patterned GaAs (311)A Substrates by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1996, 35, L297-L300.	0.8	54
39	Mono- and few-layer nanocrystalline graphene grown on Al2O3(0 0 0 1) by molecular beam epitaxy. Carbon, 2013, 56, 339-350.	5.4	54
40	Selective area growth of In(Ga)N/GaN nanocolumns by molecular beam epitaxy on GaN-buffered Si(111): from ultraviolet to infrared emission. Nanotechnology, 2013, 24, 175303.	1.3	54
41	Scaling thermodynamic model for the self-induced nucleation of GaN nanowires. Physical Review B, 2012, 85, .	1.1	53
42	Current path in light emitting diodes based on nanowire ensembles. Nanotechnology, 2012, 23, 465301.	1.3	50
43	Interface analysis of InAs/GaSb superlattice grown by MBE. Journal of Crystal Growth, 2007, 301-302, 889-892.	0.7	47
44	Self-organized quantum wires formed by elongated dislocation-free islands in (In,Ga)As/GaAs(100). Applied Physics Letters, 2001, 78, 1297-1299.	1.5	46
45	<i>In situ</i>analysis of strain relaxation during catalyst-free nucleation and growth of GaN nanowires. Nanotechnology, 2010, 21, 245705.	1.3	46
46	Collector Phase Transitions during Vaporâˆ’Solidâˆ’Solid Nucleation of GaN Nanowires. Nano Letters, 2010, 10, 3426-3431.	4.5	46
47	GaSbBi/GaSb quantum well laser diodes. Applied Physics Letters, 2017, 110, .	1.5	45
48	Reactive molecular-beam epitaxy of GaN layers directly on 6Hâ€“SiC(0001). Applied Physics Letters, 1999, 75, 944-946.	1.5	44
49	Microstructure of M-plane GaN epilayers grown on Î³-LiAlO2 by plasma-assisted molecular beam epitaxy. Philosophical Magazine Letters, 2004, 84, 435-441.	0.5	44
50	N-face GaN nanorods: Continuous-flux MOVPE growth and morphological properties. Journal of Crystal Growth, 2011, 315, 164-167.	0.7	44
51	Formation and phase transformation of Bi-containing QD-like clusters in annealed GaAsBi. Nanotechnology, 2014, 25, 205605.	1.3	44
52	Thickness dependence of the magnetic properties of MnAs films on GaAs(001) and GaAs(113)A: Role of a natural array of ferromagnetic stripes. Journal of Applied Physics, 2004, 96, 5056-5062.	1.1	42
53	Control over the Number Density and Diameter of GaAs Nanowires on Si(111) Mediated by Droplet Epitaxy. Nano Letters, 2013, 13, 3607-3613.	4.5	41
54	Optimized growth conditions for the epitaxial nucleation of Î²-GaN on GaAs(001) by molecular beam epitaxy. Applied Physics Letters, 1997, 71, 473-475.	1.5	40

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55	Decomposition in as-grown (Ga,In)(N,As) quantum wells. Applied Physics Letters, 2005, 87, 171901.	1.5	40
56	Observation of Dielectrically Confined Excitons in Ultrathin GaN Nanowires up to Room Temperature. Nano Letters, 2016, 16, 973-980.	4.5	40
57	Surfactant-mediated molecular-beam epitaxy of IIIâ€“V strained-layer heterostructures. Journal of Crystal Growth, 1995, 150, 460-466.	0.7	39
58	Monolithic integration of InGaN segments emitting in the blue, green, and red spectral range in single ordered nanocolumns. Applied Physics Letters, 2013, 102, 181103.	1.5	39
59	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 Î¼m. Applied Physics Letters, 2003, 82, 1845-1847.	1.5	38
60	Ge_{1-<i>x</i>} Mn_{<i>x</i>} Clusters: Central Structural and Magnetic Building Blocks of Nanoscale Wire-Like Self-Assembly in a Magnetic Semiconductor. Nano Letters, 2009, 9, 3743-3748.	4.5	37
61	Nanoscale Imaging of InN Segregation and Polymorphism in Single Vertically Aligned InGaN/GaN Multi Quantum Well Nanorods by Tip-Enhanced Raman Scattering. Nano Letters, 2013, 13, 3205-3212.	4.5	37
62	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. Applied Physics Letters, 2003, 82, 3451-3453.	1.5	36
63	Critical Role of Two-Dimensional Island-Mediated Growth on the Formation of Semiconductor Heterointerfaces. Physical Review Letters, 2012, 109, 126101.	2.9	35
64	Anomalous Strain Relaxation in Coreâ€“Shell Nanowire Heterostructures via Simultaneous Coherent and Incoherent Growth. Nano Letters, 2017, 17, 136-142.	4.5	35
65	Device quality submicron arrays of stacked sidewall quantum wires on patterned GaAs (311)A substrates. Applied Physics Letters, 1998, 72, 2002-2004.	1.5	34
66	Structural properties of GaN layers on Si(001) grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1998, 83, 3800-3806.	1.1	34
67	Correlation between interface structure and light emission at 1.3â€“1.55 Î¼m of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2195.	1.6	34
68	Growth of freestanding GaN using pillar-epitaxial lateral overgrowth from GaN nanocolumns. Journal of Crystal Growth, 2007, 309, 113-120.	0.7	34
69	Insight into the Growth and Control of Single-Crystal Layers of Geâ€“Sbâ€“Te Phase-Change Material. Crystal Growth and Design, 2011, 11, 4606-4610.	1.4	34
70	Selective area growth and characterization of InGaN nano-disks implemented in GaN nanocolumns with different top morphologies. Applied Physics Letters, 2012, 100, .	1.5	34
71	Strong alignment of self-assembling InP quantum dots. Physical Review B, 1996, 54, 4913-4918.	1.1	33
72	Strain accommodation in Ga-assisted GaAs nanowires grown on silicon (111). Nanotechnology, 2012, 23, 305703.	1.3	33

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73	Observation of atomic ordering of triple-period-A and -B type in GaAsBi. Applied Physics Letters, 2014, 105, 041602.	1.5	33
74	Formation of Quasicrystalline AlCuFe by Physical Vapor Deposition: Phase Selection via Nanocluster Nucleation. Physical Review Letters, 1997, 78, 262-265.	2.9	32
75	Heteroepitaxy of dissimilar materials: effect of interface structure on strain and defect formation. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1119-1125.	1.3	32
76	Plasmon excitation in electron energy-loss spectroscopy for determination of indium concentration in (In,Ga)N/GaN nanowires. Nanotechnology, 2012, 23, 485701.	1.3	32
77	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. Journal of Crystal Growth, 2003, 251, 383-387.	0.7	31
78	Molecular-beam epitaxy of InSb/GaSb quantum dots. Journal of Applied Physics, 2007, 101, 124309.	1.1	31
79	Epitaxial growth and characterization of InN nanorods and compact layers on silicon substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 1490-1493.	0.7	30
80	Formation of High-Quality GaN Microcrystals by Pendeoepitaxial Overgrowth of GaN Nanowires on Si(111) by Molecular Beam Epitaxy. Crystal Growth and Design, 2011, 11, 4257-4260.	1.4	30
81	Strain Relief of Heteroepitaxial bcc-Fe(001) Films. Physical Review Letters, 2004, 93, 236101.	2.9	29
82	Polarity determination by electron energy-loss spectroscopy: application to ultra-small III-nitride semiconductor nanocolumns. Nanotechnology, 2011, 22, 415701.	1.3	29
83	Emission control of InGaN nanocolumns grown by molecular-beam epitaxy on Si(111) substrates. Applied Physics Letters, 2011, 99, .	1.5	29
84	Epitaxial phaseâ€change materials. Physica Status Solidi - Rapid Research Letters, 2012, 6, 415-417.	1.2	29
85	Interplay between Surface Stabilization, Growth Mode and Strain Relaxation during Molecular-Beam Epitaxy of Highly Mismatched III-V Semiconductor Layers. Europhysics Letters, 1994, 25, 663-668.	0.7	28
86	Chapter 7 Crystal Structure of Group III Nitrides. Semiconductors and Semimetals, 1997, 50, 167-192.	0.4	28
87	AlGaN Nanocolumns and AlGaN/GaN/AlGaN Nanostructures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 234, 717-721.	0.7	27
88	MnAs nanoclusters embedded in GaAs: synthesis and properties. Applied Surface Science, 2004, 234, 16-21.	3.1	27
89	Spontaneous formation of three-dimensionally ordered Bi-rich nanostructures within GaAs_{1âˆ’<i>x</i>}Bi_{<i>x</i>}/GaAs quantum wells. Nanotechnology, 2016, 27, 325603.	1.3	27
90	High-density, uniform InSbâˆ•GaSb quantum dots emitting in the midinfrared region. Applied Physics Letters, 2006, 89, 263118.	1.5	26

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91	Enhanced Performances of Quantum Dot Lasers Operating at 1.3 mu m. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1188-1196.	1.9	26
92	High-quality distributed Bragg reflectors based on AlxGa1â^'xN/GaN multilayers grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 2136-2138.	1.5	25
93	Spontaneous formation of nanostructures by surface spinodal decomposition in GaAs1â^'xBix epilayers. Journal of Applied Physics, 2015, 117, .	1.1	25
94	Defect control during growth of highly mismatched (100). Journal of Crystal Growth, 1995, 146, 368-373.	0.7	24
95	Indentation of GaN: A Study of the Optical Activity and Strain State of Extended Defects. Physica Status Solidi A, 2002, 192, 79-84.	1.7	24
96	Nitrogen-dependent optimum annealing temperature of Ga(As,N). Journal of Crystal Growth, 2004, 267, 60-66.	0.7	24
97	Epitaxial Heusler alloy films on GaAs(001) substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 371-374.	1.3	24
98	Growth temperature dependent interfacial reaction of Heusler-alloy Co2FeSi/GaAs(001) hybrid structures. Journal Physics D: Applied Physics, 2007, 40, 1631-1634.	1.3	24
99	Indium distribution at the interfaces of (Ga,In)(N,As)â^•GaAs quantum wells. Applied Physics Letters, 2008, 92, .	1.5	24
100	Interface engineering for improved growth of GaSb on Si(111). Journal of Crystal Growth, 2011, 323, 401-404.	0.7	24
101	Nitrogen-enhanced indium segregation in (Ga,In)(N,As)/GaAs multiple quantum wells grown by molecular-beam epitaxy. New Journal of Physics, 2007, 9, 405-405.	1.2	23
102	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1739-1744.	0.7	23
103	Structural characterization of thin GaN epilayers directly grown on on-axis 6Hâ€"SiC(0001) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 3869-3871.	1.5	22
104	Structural and optical characterization of thick InGaN layers and InGaN/GaN MQW grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 131-134.	1.7	22
105	Growth of Fe3Si/Ge/Fe3Si trilayers on GaAs(001) using solid-phase epitaxy. Applied Physics Letters, 2017, 110, .	1.5	22
106	Green photoluminescence from cubic In0.4Ga0.6N grown by radio frequency plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1998, 73, 1230-1232.	1.5	21
107	Properties of cubic (In,Ga)N grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 73-79.	1.7	20
108	Epitaxial Fe3Si/Ge/Fe3Si thin film multilayers grown on GaAs(001). Thin Solid Films, 2014, 556, 120-124.	0.8	20

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109	Lateral piezoelectric fields in strained semiconductor heterostructures. Physical Review B, 1994, 50, 17111-17119.	1.1	19
110	Optical properties of heavily dopedGaN/(Al,Ga)Nmultiple quantum wells grown on6Hâˆ'SiC(0001)by reactive molecular-beam epitaxy. Physical Review B, 2000, 61, 16025-16028.	1.1	19
111	Toward edges-rich MoS₂ layers via chemical liquid exfoliation triggering distinctive magnetism. Materials Research Letters, 2017, 5, 267-275.	4.1	19
112	Properties of cubic GaN grown by MBE. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 215-221.	1.7	18
113	Atomically engineered interfaces for spin injection: ultrathin epitaxial Fe films grown on As- and Ga-terminated GaAs(001) substrates. Applied Surface Science, 2004, 237, 181-188.	3.1	18
114	Ferromagnetic Ge(Mn) nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 422-425.	1.3	18
115	Nanofocus x-ray diffraction and cathodoluminescence investigations into individual coreâ€"shell (In,Ga)N/GaN rod light-emitting diodes. Nanotechnology, 2016, 27, 325707.	1.3	18
116	Polarity-Induced Selective Area Epitaxy of GaN Nanowires. Nano Letters, 2017, 17, 63-70.	4.5	18
117	Crystal Phase Control during Epitaxial Hybridization of IIIâ€V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	2.6	18
118	Anisotropic misfit dislocation nucleation in two-dimensional grown InAs/GaAs(001) heterostructures. Applied Physics Letters, 1998, 73, 1074-1076.	1.5	17
119	Molecular beam epitaxial growth window for high-quality (Ga,In)(N,As) quantum wells for long wavelength emission. Applied Physics Letters, 2006, 88, 191115.	1.5	17
120	Correlation among Growth Conditions, Morphology, and Optical Properties of Nanocolumnar InGaN/GaN Heterostructures Selectively Grown by Molecular Beam Epitaxy. Crystal Growth and Design, 2015, 15, 2661-2666.	1.4	17
121	Study of 3D-growth conditions for selective area MOVPE of high aspect ratio GaN fins with non-polar vertical sidewalls. Journal of Crystal Growth, 2017, 476, 90-98.	0.7	17
122	Excitonic properties of isolated nanometerâ€sized InAs islands in a GaAs matrix. Journal of Applied Physics, 1995, 78, 1980-1983.	1.1	16
123	MBE-grown high-quality (Al,Ga)N/GaN distributed Bragg reflectors for resonant cavity LEDs. Semiconductor Science and Technology, 2001, 16, 913-917.	1.0	16
124	Critical parameters for the molecular beam epitaxial growth of 1.55Î¼m (Ga,In)(N,As) multiple quantum wells. Applied Physics Letters, 2006, 89, 181910.	1.5	16
125	Striated surface morphology and crystal orientation of m-plane GaN films grown on Î³-LiAlO2(100). Applied Physics Letters, 2010, 96, 231914.	1.5	16
126	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. Applied Physics Letters, 2013, 102, .	1.5	16

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127	Plan-view transmission electron microscopy investigation of GaAs/(In,Ga)As core-shell nanowires. Applied Physics Letters, 2014, 105, 121602.	1.5	16
128	Detecting lateral composition modulation in dilute Ga(As,Bi) epilayers. Nanotechnology, 2015, 26, 425701.	1.3	16
129	Interface structure and strain state of InAs nano-clusters embedded in silicon. Acta Materialia, 2015, 90, 133-139.	3.8	16
130	InAs/GaSb short-period superlattice injection lasers operating in 2.5â€…[micro sign]mâ€“3.5â€…[micro sign]m mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	0.5	15
131	Impact of carrier localization on the photoluminescence characteristics of (Ga,In)(N,As) and (Ga,In)(N,As,Sb) quantum wells. Journal of Applied Physics, 2008, 104, .	1.1	15
132	Monodisperse (In, Ga)N insertions in catalyst-free-grown GaN(0001) nanowires. Nanotechnology, 2011, 22, 365703.	1.3	15
133	<i>In situ</i> doping of catalyst-free InAs nanowires with Si: Growth, polytypism, and local vibrational modes of Si. Applied Physics Letters, 2013, 103, .	1.5	15
134	Selective area growth and characterization of GaN nanocolumns, with and without an InGaN insertion, on semi-polar (11â€“22) GaN templates. Applied Physics Letters, 2013, 103, .	1.5	15
135	Thermal expansion of single-crystalline <i>Î²</i>-Ga2O3 from RT to 1200â€‰K studied by synchrotron-based high resolution x-ray diffraction. Applied Physics Letters, 2018, 113, .	1.5	15
136	Efficiency optimization of p-type doping in GaN:Mg layers grown by molecular-beam epitaxy. Journal of Crystal Growth, 2004, 270, 542-546.	0.7	14
137	Epitaxial growth of 6H-AlN on M-plane SiC by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2007, 300, 127-129.	0.7	14
138	Epitaxial growth and structure of (La1â^’xLux)2O3 alloys on Si(111). Applied Physics Letters, 2010, 97, 031911.	1.5	14
139	Delayed crystallization of ultrathin Gd2O3 layers on Si(111) observed by in situ X-ray diffraction. Nanoscale Research Letters, 2012, 7, 203.	3.1	14
140	Counterintuitive strain distribution in axial (In,Ga)N/GaN nanowires. Applied Physics Letters, 2016, 108, .	1.5	14
141	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. Applied Physics Letters, 2018, 112, .	1.5	14
142	Excitonic Aharonovâ€“Bohm Oscillations in Coreâ€“Shell Nanowires. Advanced Materials, 2019, 31, 1805645.	11.1	14
143	Coaxial GaAs/(In,Ga)As Dot-in-a-Well Nanowire Heterostructures for Electrically Driven Infrared Light Generation on Si in the Telecommunication O Band. ACS Applied Nano Materials, 2020, 3, 165-174.	2.4	14
144	Growth, interface structure, and magnetic properties of Fe/GaAs and Fe3Si/GaAs hybrid systems. International Journal of Materials Research, 2006, 97, 1026-1036.	0.1	13

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145	Effect of indium incorporation on optical and structural properties of m-plane InGaN/GaN MQW on LiAlO2 substrates. Journal of Crystal Growth, 2011, 315, 246-249.	0.7	13
146	GaAsâ€“Fe₃Si Coreâ€“Shell Nanowires: Nanobar Magnets. Nano Letters, 2013, 13, 6203-6209.	4.5	13
147	Magnetic properties of Gdâ€doped GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 1673-1684.	0.7	13
148	Growth and stability of rocksalt Zn1â^'xMgxO epilayers and ZnO/MgO superlattice on MgO (100) substrate by molecular beam epitaxy. Journal of Chemical Physics, 2016, 144, 214704.	1.2	13
149	Interfacial reactions during the molecular beam epitaxy of GaN nanowires on Ti/Al₂O₃. Nanotechnology, 2019, 30, 114001.	1.3	13
150	MBE growth and characteristics of cubic GaN. Thin Solid Films, 1997, 306, 231-236.	0.8	12
151	Linear increase of the modal gain in 1.3 Âµm InAs/GaAs quantum dot lasers containing up to seven-stacked QD layers. Nanotechnology, 2008, 19, 275401.	1.3	12
152	Epitaxial Heusler alloy Co₂FeSi films on Si(1â€‰1â€‰1) substrates grown by molecular beam epitaxy. Journal Physics D: Applied Physics, 2010, 43, 305004.	1.3	12
153	Structure and Composition of Isolated Core-Shell<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mi>In</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq1 1 0.784314 rg mathvariant="normal">N</mml:mi><mml:mo>/</mml:mo><mml:mi>GaN</mml:mi></mml:mrow></mml:math>Rods Based on Nanofocus X-Ray Diffraction and Scanning Transmission Electron Microscopy. Physical Revie	1.5	12
154	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. Acta Materialia, 2018, 143, 121-129.	3.8	12
155	Growth mode evolution during (100)-oriented <i>Î²</i>-Ga₂O₃ homoepitaxy. Nanotechnology, 2018, 29, 395705.	1.3	12
156	SnO/Î²-Ga2O3 heterojunction field-effect transistors and vertical pâ€“n diodes. Applied Physics Letters, 2022, 120, .	1.5	12
157	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. Physica Status Solidi (B): Basic Research, 2007, 244, 2683-2696.	0.7	11
158	Oxygen-Deficient Oxide Growth by Subliming the Oxide Source Material: The Cause of Silicide Formation in Rare Earth Oxides on Silicon. Crystal Growth and Design, 2013, 13, 3645-3650.	1.4	11
159	Electron tomography on nanopores embedded in epitaxial GaSb thin films. Micron, 2015, 73, 54-62.	1.1	11
160	Strategies for Analyzing Noncommonâ€Atom Heterovalent Interfaces: The Case of CdTeâ€onâ€InSb. Advanced Materials Interfaces, 2020, 7, 1901658.	1.9	11
161	Gallium nitride heterostructures on 3D structured silicon. Nanotechnology, 2008, 19, 405301.	1.3	10
162	Morphology and stress evolution of InAs QD grown and annealed in-situ at high temperature. Journal of Crystal Growth, 2010, 312, 447-451.	0.7	10

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